

[illegible]

04/24/2019 12:01 PM

 **Drafts**

3 BRS:

3 BRS:

3 BRS:

• BRS: knallt

3 BRS: 19 21 23

♡ BRS: 32with 33

⊙ Pending

Active

...L1: (0) 10/713510

• L2: (1) 10/165510

*913: (719429) ({ ferr?magnetic ferr? adj magnetic } ((magnetic) (magn-

4: (940832) (sidewall side adj (wall surface))

• L5: (3154405) conductive conductor electrode contact

☞ L8: (26355) L4 near L5

*9 L7: (719878) memory

LB: (548) L8 with L7

→ L9 (64) L8 and L3

Failed

 Saved

52: (1) 09/948877

53: (1736) "KONINKLIJKE PHILIPS".a3.

.. S4: (0) 12/6985-14

.. S5: (0) 10/705504

1000 1000 1000 1000

END: 12509PIR, 12502V, 12017R

1990-1991

L8 and L3

Feb, 2005

	U.S.	Inventor	Document	Issue P.	Title	Current	Current X	Retrieval	S	C	P	Image Do P
1	<input type="checkbox"/>	Lowrey, Ty	US 676489	2004	4	Method of making programmable resis	438/23	438/381		<input type="checkbox"/>	<input type="checkbox"/>	US 676489
2	<input type="checkbox"/>	Nejad, Has	US 200500	2005	7	Methods of forming magnetoresistive	438/3			<input type="checkbox"/>	<input type="checkbox"/>	US 20050
3	<input type="checkbox"/>	Maimon, Jo	US 200500	2005	2	Programmable resistance memory ele	257/2			<input type="checkbox"/>	<input type="checkbox"/>	US 20050
4	<input type="checkbox"/>	Lowrey, Ty	US 200500	2005	4	Programmable resistance memory ele	438/20			<input type="checkbox"/>	<input type="checkbox"/>	US 20050
5	<input type="checkbox"/>	Anthony, T	US 200402	2004	9	Magnetic memory	365/17			<input type="checkbox"/>	<input type="checkbox"/>	US 20040
6	<input type="checkbox"/>	Kostylev, S	US 200402	2004	4	Electrically programmable memory ele	257/53			<input type="checkbox"/>	<input type="checkbox"/>	US 20040
7	<input type="checkbox"/>	Lowrey, Ty	US 200402	2004	3	Electrically programmable memory ele	257/53			<input type="checkbox"/>	<input type="checkbox"/>	US 20040
8	<input type="checkbox"/>	Kim, Eun-Si	US 200402	2004	1	High density magnetoresistance mem	365/17	365/171		<input type="checkbox"/>	<input type="checkbox"/>	US 20040
9	<input type="checkbox"/>	Hsu, Sheng	US 200402	2004	2	High-density SOI cross-point memory	438/70			<input type="checkbox"/>	<input type="checkbox"/>	US 20040
10	<input type="checkbox"/>	Lowrey, Ty	US 200401	2004	6	Method for making programmable res	438/95	257/E27.0		<input type="checkbox"/>	<input type="checkbox"/>	US 20040